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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/707,704	01/06/2004	HANN-JYE HSU	11964-US-PA	1703	
31561	7590 12/15/2005		EXAMINER		
JIANQ CHYUN INTELLECTUAL PROPERTY OFFICE			ERDEM, FAZLI		
7 FLOOR-1, NO. 100 ROOSEVELT ROAD, SECTION 2 TAIPEI, 100			ART UNIT	PAPER NUMBER	
			2826		
TAIWAN			DATE MAILED: 12/15/2005	DATE MAILED: 12/15/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)				
	10/707,704	HSU ET AL.				
Office Action Summary	Examiner	Art Unit				
	Fazli Erdem	2826				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DATE - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  If NO period for reply is specified above, the maximum statutory period was really reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be timulated will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE!	√. nely filed the mailing date of this communication. D (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on 29 Section 29 Section 1)	eptember 2005.					
2a) ☐ This action is <b>FINAL</b> . 2b) ☐ This						
Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 45	53 O.G. 213.				
Disposition of Claims						
4)⊠ Claim(s) <u>9-11 and 14-18</u> is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>9-11 and 14-18</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/o	r election requirement.					
Application Papers						
9)☐ The specification is objected to by the Examine	er.					
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11)☐ The oath or declaration is objected to by the Ex	caminer. Note the attached Office	Action or form PTO-152.				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicat nity documents have been receive u (PCT Rule 17.2(a)).	ion No ed in this National Stage				
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:					

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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 9-11 and 14-18 rejected under 35 U.S.C. 103(a) as being unpatentable over Chang et al. (6,754,105) in view of Yoshikawa (6,335,554)) further in view of Forbes et al. (2004/0004245) further in view of Kang et al. (6,963,108)

Regarding Claims 9-12 and 15-18, Chang et al. disclose a trench sidewall charge trapping dielectric flash memory device where in Fig. 2, it is disclosed trench structures 46 disposes inside p-well 54. Gates 66a and 66b are completely covered with dielectric layer 48. This dielectric layer 48 is between the charge trapping layers 50b' and 50a'. Furthermore, dielectric layer 58 is outside charge trapping layers. Source/drain regions are labeled 62a and 62b. Change et al. fail to disclose the required plurality of lightly doped regions under plurality of SiN spacers, the required source/drain regions on both sides of the trench and the required conformal charge trapping layer. However, Yoshikawa discloses a memory device where in Fig. 1, plurality of lightly doped regions 10 are under the plurality of SiN spacers 4A and 4B. Furthermore, Forbes et al. disclose a memory utilizing oxide-conductor nanolamination where in Fig. 3, source/drain regions 302-1 and 302-2 are located on both sides of trench 340. Finally, Kang et al. disclose a

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recessed channel where in Figs. 2A and 2B, the required conformal charge trapping layer 160b is disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required plurality of lightly doped regions under the plurality of SiN spacers, the source/drain regions on both sides of trench and the required conformal charge trapping layer in Chang et al. as taught by Hwang, Forbes and Kang et al. respectively, in order to have a semiconductor memory structure with better performance.

## Conclusion

3. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE December 9, 2005

